



InGaAs PIN Photodiode

Type: PDS453-02

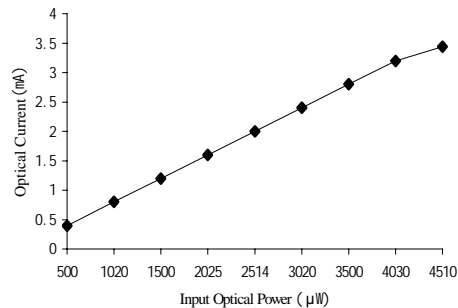
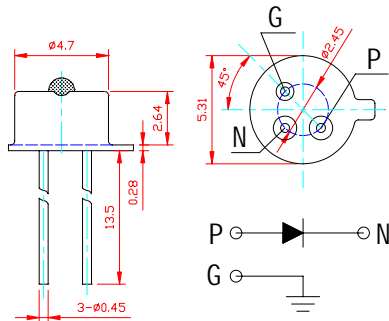
ELECTRO-OPTICAL CHARACTERISTICS(T=25):

PARAMETERS	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Wavelength			1000		1650	nm
Dark Current	I_D	$E_e=0, V_R=5V$		0.5	1	nA
Responsivity ⁽¹⁾	R_e	$V_R=5V, \lambda=1310nm$	0.85	0.90		A/W
Responsivity ⁽²⁾	R_e	$V_R=5V, \lambda=1550nm$	0.90	0.95		A/W
Capacitance	C	$f=1MHz, case grounded, V_R=5V E_e=0$		5	6	pF
Operating voltage	V_{opr}			-5	-15	V
Rise& fall time	T_r, T_f	-5V			3	ns

Note:(1),(2) For parallel beam application .Responsivity measure by Collimator.

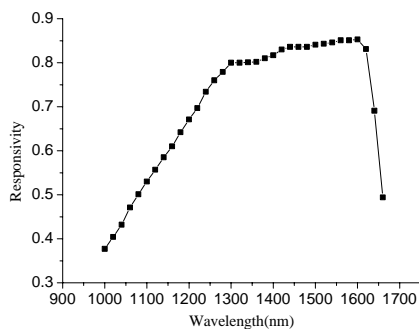
ABSOLUTE MAXIMUM RATINGS(T=25):

PARAMETERS	MIN	MAX	UNIT
Reverse Voltage		25	V
Forward Current		10	mA
Operating Temperature	-40	+85	
Storage Temperature	-40	+85	
Lead Solder Temperature		260	
Lead soldering duration		10	s

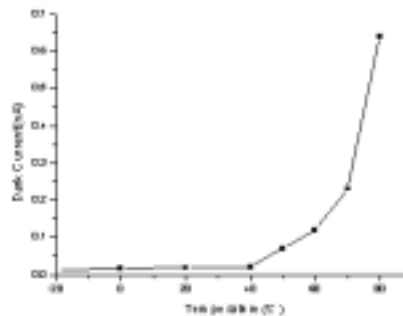


Package Dimensions

Current-Optical Power Curve



Spectrum Curve



Dark Current-Temperature Curve

PRECAUTIONS:

- ESD protection is imperative.
- Please shorten the length of the devices leads as much as possible.

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